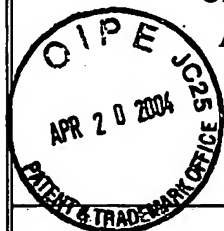


INFORMATION DISCLOSURE CITATION IN AN APPLICATION



(PTO-1449)

 ATTY. DOCKET NO.
63979-032

 SERIAL NO.
10/643,944

 APPLICANT
Yoshiaki HASEGAWA, et al.

 FILING DATE
August 20, 2003

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2828

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
RM		US 5,345,463	09/08/1994	Mannoh et al.	
		US			
		US			
		US			
		US			

FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes-Number + Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No
RM		JP 10-200214 A	07/31/1998	NEC CORP			X
RM		JP 6-283825 A	10/07/1994	TOYODA GOSEI CO., LTD.			X
RM		JP 4-275478 A	10/01/1992	NEC CORP.			X
RM		JP 2000-21789	01/21/2000	TOSHIBA CORP.			X
RM		JP 5-291686	11/05/1993				X
RM		JP 11-251687	09/17/1999				X

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
RM		GOTO, S., et al. "InGaN: Improvement of quantum efficiency by InGaN Interlayer for blue-violet laser diodes." Sony Shiroishi Semiconductor Inc. 28p-E-12, Page 369
RM		NAKAMURA, Shuji. "InGaN Multiquantum-Well-Structure Laser Diodes with GaN-AlGaIn Modulation -Doped Strained-Layer Superlattices." IEEE Journal of Selected Topics In Quantum Electronics, Vol. 4, No.3, May/June 1998, pp. 483-489
RM		KNEISSL, Michael., et al. "Performance and degradation of continuous-wave InGaN multiple-quantum-well laser diodes on epitaxially laterally overgrown GaN substrates." Applied Physics Letters, Volume 77, Number 13, September 25, 2000, pp. 1931-1933
RM		NAKAMURA, Shuji., et al. "UV/Blue/Green InGaN-Based LEDs and Laser Diodes Grown on Epitaxially Laterally Overgrown GaN." IEICE Trans. Electron., Vol E83-C, No. 4, April 2000, pp. 529-535
RM		TOJYO, Tsuyoshi., et al. "GaN-Based High Power Blue-Violet Laser Diodes." The Japan Society for Applied Physics, Volume 40, Part 1. No. 5A, May 2001, pp.3208-3210
RM		KURODA, Naotaka., et al. "Precise control of pn-junction profiles for GaN-based LD structures using GaN substrates with low dislocation densities." Journal of Crystal Growth 189/190 (1998) pp. 551-555
RM		OHBA, Y., et al. "A study on strong memory effects for Mg doping GaN metalorganic chemical vapor deposition." Journal of Crystal growth 145 (1994) pp. 214-218
RM		BLAAUW, C., et al. "Secondary ion mass spectrometry and electrical characterization of Zn diffusion in n-type InP." J. Appl. Phys. 66(2), July 15, 1989, American Institute of Physics, pp. 605610

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